

Silicon PNP Power Transistors

2SA671

DESCRIPTION

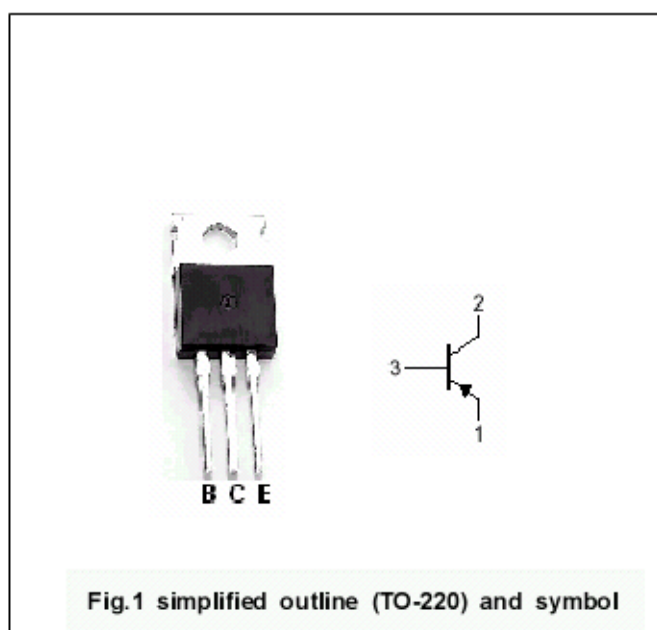
- With TO-220 package
 - Complement to type 2SC1061
 - Low collector saturation voltage
- Note: type 2SA670 with short pin

APPLICATIONS

- Designed for use in low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector; connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-50	V
V_{CEO}	Collector-emitter voltage	Open base	-50	V
V_{EBO}	Emitter-base voltage	Open collector	-4	V
I_C	Collector current		-3	A
I_{CM}	Collector current-peak		-6	A
I_B	Base current		-0.5	A
P_C	Collector power dissipation	$T_C=25^{\circ}\text{C}$	25	W
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\text{-}j\text{-}c}$	Thermal resistance from junction to case	5.0	$^{\circ}\text{C}/\text{W}$

**Silicon PNP Power Transistors****2SA671****CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA, I _B =0	-50			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-5mA, I _C =0	-7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2A; I _B =-0.2A			-1.0	V
V _{BE}	Base-emitter on voltage	I _C =-1A; V _{CE} =-4V			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-25V; I _E =0			-100	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-4V; I _C =0			-100	μ A
h _{FE-1}	DC current gain	I _C =-0.1A; V _{CE} =-4V	35		320	
h _{FE-2}	DC current gain	I _C =-1A; V _{CE} =-4V	35			
f _T	Transition frequency	I _C =-0.5A; V _{CE} =-4V	5.0			MHz

◆ h_{FE-1} Classifications

A	B	C	D
35-70	60-120	100-200	160-320



PACKAGE OUTLINE

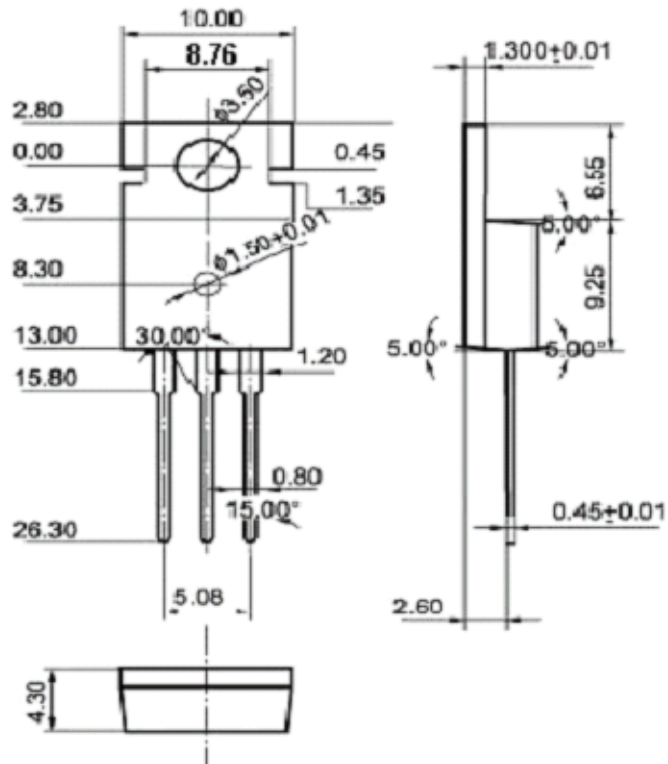


Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)